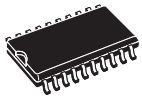
74LVX245

LOW VOLTAGE CMOS OCTAL BUS TRANSCEIVER (3-STATE) WITH 5V TOLERANT INPUTS

- HIGH SPEED:
  t_{PD}=4.7ns (TYP.) at V_{CC} = 3.3V
- 5V TOLERANT INPUTS
- POWER-DOWN PROTECTION ON INPUTS
- INPUT VOLTAGE LEVEL:
  V_{IL} = 0.8V, V_{IH} = 2V at V_{CC} =3V
- LOW POWER DISSIPATION:
  I_{CC} = 4 µA (MAX.) at T_A=25°C
- LOW NOISE:
  V_{OLP} = 0.5V (TYP.) at V_{CC} =3.3V
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN) at V_{CC} =3V
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
  V_{CC}(OPR) = 2V to 3.6V (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 245
- IMPROVED LATCH-UP IMMUNITY



SOP

TSSOP

ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVX245M	74LVX245MTR
TSSOP		74LVX245TTR

DESCRIPTION

The 74LVX245 is a low voltage CMOS OCTAL BUS BUFFER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power, battery operated and low noise 3.3V applications.

This IC is intended for two-way asynchronous communication between data busses; the direction of data transmission is determined by DIR input. The enable input $\overline{G}$ can be used to disable the device so that the busses are effectively isolated.

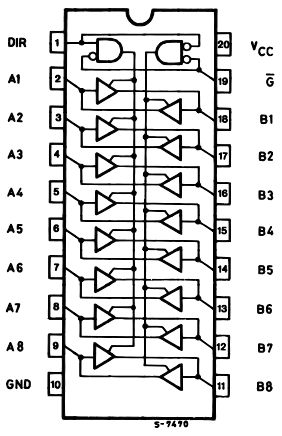
Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

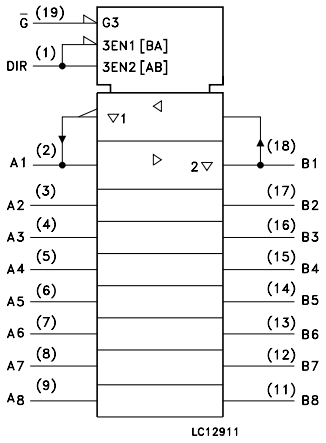
This device can be used to interface 5V to 3V. It combines high speed performance with the true CMOS low power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

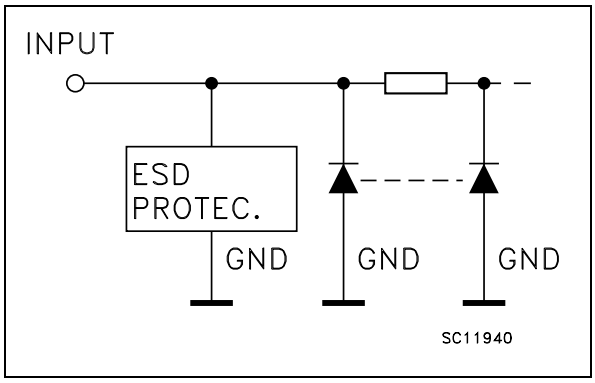
All floating bus terminals during High Z state must be held HIGH or LOW.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	DIR	Directional Control
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs/Outputs
18, 17, 16, 15, 14, 13, 12, 11	B1 to B8	Data Inputs/Outputs
19	$\overline{G}$	Output Enable Input
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		FUNCTION		OUTPUT
$\overline{G}$	DIR	A BUS	B BUS	
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X :Don't Care
Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	- 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2) (V_{CC} = 3V)	0 to 100	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V
2) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0		2.0			2.0		2.0		
		3.6		2.4			2.4		2.4		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0				0.8		0.8		0.8	
		3.6				0.8		0.8		0.8	
V_{OH}	High Level Output Voltage	2.0	I_O=-50 µA	1.9	2.0		1.9		1.9		V
		3.0	I_O=-50 µA	2.9	3.0		2.9		2.9		
		3.0	I_O=-4 mA	2.58			2.48		2.4		
V_{OL}	Low Level Output Voltage	2.0	I_O=50 µA		0.0	0.1		0.1		0.1	V
		3.0	I_O=50 µA		0.0	0.1		0.1		0.1	
		3.0	I_O=4 mA			0.36		0.44		0.55	
I_{OZ}	High Impedance Output Leakage Current	3.6	$V_I = V_{IH}$ or V_{IL} $V_O = V_{CC}$ or GND			±0.25		± 2.5		± 5	µA
I_I	Input Leakage Current	3.6	V_I = 5V or GND			± 0.1		± 1		± 1	µA
I_{CC}	Quiescent Supply Current	3.6	$V_I = V_{CC}$ or GND			4		40		40	µA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C_L = 50 pF		0.5	0.8					V
V_{OLV}				-0.8	-0.5						
V_{IHD}	Dynamic High Voltage Input (note 1, 3)	3.3		2.0							
V_{ILD}	Dynamic Low Voltage Input (note 1, 3)	3.3				0.8					

1) Worst case package.
2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.
3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

Symbol	Parameter	Test Condition			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	2.7	15			6.1	11.4	1.0	13.5	1.0	15.0	ns
		2.7	50			8.6	14.9	1.0	17.0	1.0	18.0	
		3.3(*)	15			4.5	7.1	1.0	8.5	1.0	9.5	
		3.3(*)	50			7.2	10.6	1.0	12.0	1.0	13.0	
t_{PZL} t_{PZH}	Output Enable Time	2.7	15			7.1	13.8	1.0	16.5	1.0	17.5	ns
		2.7	50			9.6	17.3	1.0	20.0	1.0	21.0	
		3.3(*)	15			5.5	8.8	1.0	10.5	1.0	12.	
		3.3(*)	50			8.0	12.3	1.0	14.0	1.0	15.0	
t_{PLZ} t_{PHZ}	Output Disable Time	2.7	50			11.6	16.0	1.0	19.0	1.0	20.5	ns
		3.3(*)	50			9.7	11.4	1.0	13.0	1.0	14.5	
t_{OSLH} t_{OSHL}	Output to Output Skew Time (note 1,2)	2.7	50			0.5	1.0		1.5		1.5	ns
		3.3(*)	50			0.5	1.0		1.5		1.5	

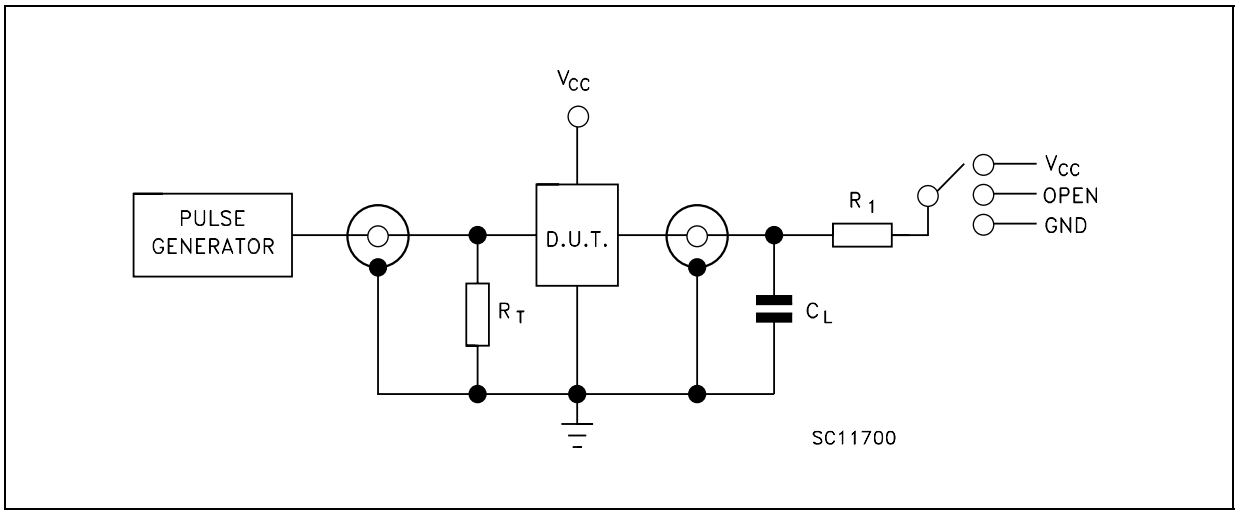
1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW
2) Parameter guaranteed by design
(*) Voltage range is 3.3V ± 0.3V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	3.3			5			10		10	pF
$C_{i/o}$	Input/Output Capacitance	3.3			10			15		15	pF
C_{PD}	Power Dissipation Capacitance (note 1)	3.3	f_{IN} = 10MHz		32						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

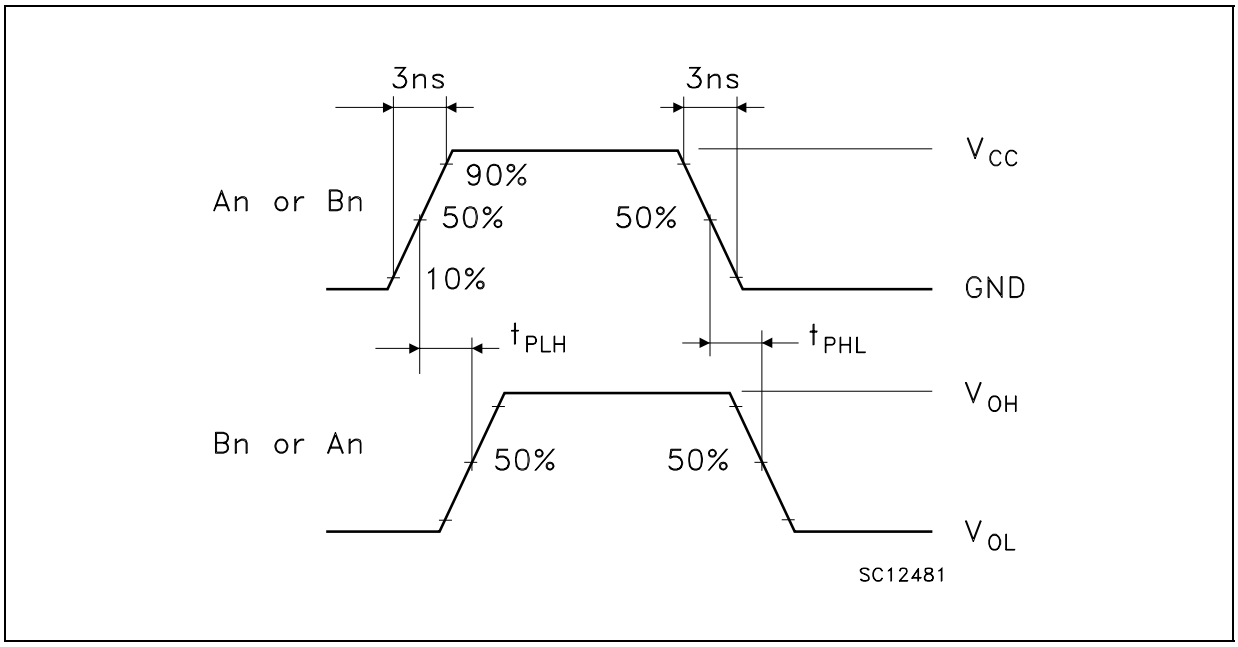
TEST CIRCUIT



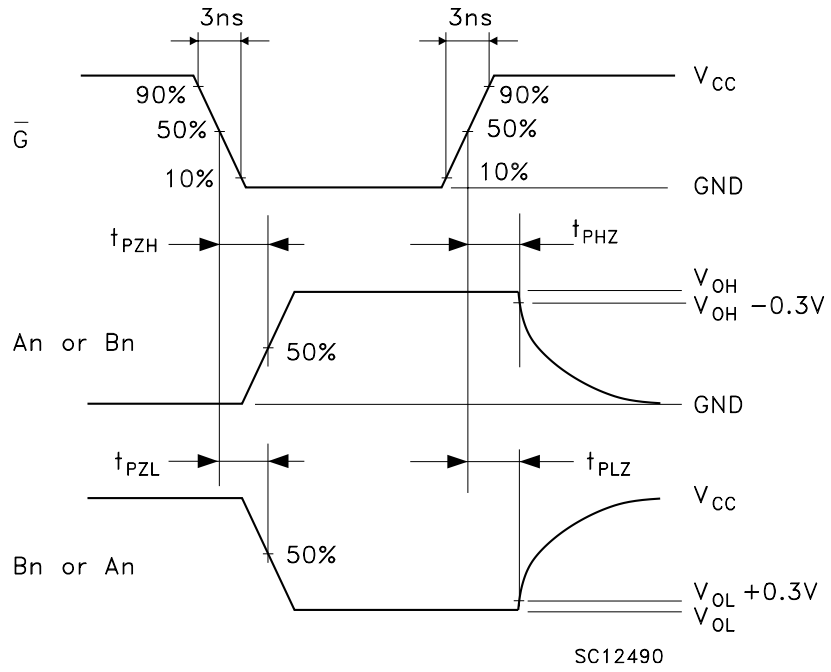
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	V_{CC}
t_{PZH}, t_{PHZ}	GND

C_L =15/50pF or equivalent (includes jig and probe capacitance)
R_L = R1 = 1KΩ or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

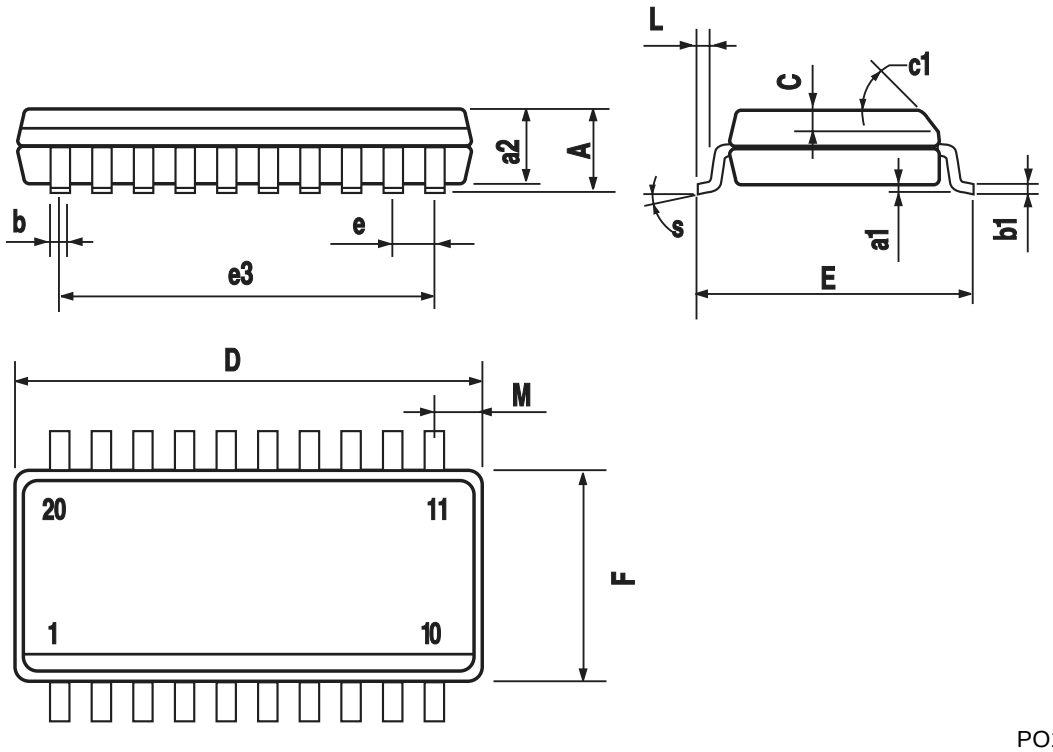


WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



PO13L

TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030